

## CORRECTION

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## Correction: Broadband ultrafast photovoltaic detectors based on large-scale topological insulator Sb<sub>2</sub>Te<sub>3</sub>/STO heterostructures

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Correction for 'Broadband ultrafast photovoltaic detectors based on large-scale topological insulator Sb<sub>2</sub>Te<sub>3</sub>/STO heterostructures' by Honghui Sun, *et al.*, *Nanoscale*, 2017, 9, 9325–9332.

The authors have noticed an error in the published version of this manuscript. The sentence beginning “Due to the difference in doping concentration between Sb<sub>2</sub>Te<sub>3</sub> ( $N_h \sim 2 \text{ synth } 10^{19} \text{ cm}^{-3}$ )...” should be corrected to “Due to the difference in doping concentration between Sb<sub>2</sub>Te<sub>3</sub> ( $N_h \sim 2 \times 10^{19} \text{ cm}^{-3}$ )...”

In the revised sentence, the word “synth” has been changed to “ $\times$ ”.

The Royal Society of Chemistry apologises for these errors and any consequent inconvenience to authors and readers.

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